IGBT - NPT

1200 V, 40 A

FGH40N120AN

Description

Employing NPT technology, ON Semiconductor's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

Features

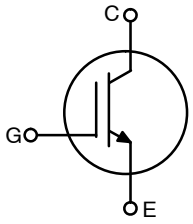
- High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)}$ = 2.6 V @ I_C = 40 A
- High Input Impedance
- This Device is Pb−Free and is RoHS Compliant

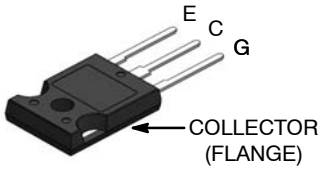
Applications

- Induction Heating, UPC, AC & DC Motor Controls and General Purpose Inverters

ON Semiconductor®

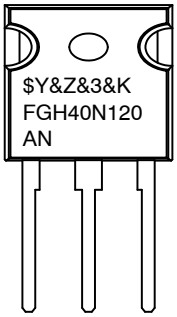
www.onsemi.com





TO−247−3LD
CASE 340CK

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH40N120AN	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

© Semiconductor Components Industries, LLC, 2006

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter		Symbol	FGH40N120AN	Unit
Collector to Emitter Voltage		V_{CES}	1200	V
Gate to Emitter Voltage		V_{GES}	±25	V
Collector Current	T_C = 25°C	I_C	64	A
Collector Current	T_C = 100°C		40	A
Pulsed Collector Current		I_{CM} (Note 1)	160	A
Maximum Power Dissipation	T_C = 25°C	P_D	417	W
Maximum Power Dissipation	T_C = 100°C		167	W
Short Circuit Withstand Time, V_{CE} = 600 V, V_{GE} = 15 V, T_C = 125°C		SCWT	10	μs
Operating Junction Temperature		T_J	−55 to +150	°C
Storage Temperature Range		T_{STG}	−55 to +150	°C
Maximum Lead Temp. for Soldering Purposes, 1/8” from Case for 5 Seconds		T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$(IGBT)	–	0.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	–	40	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH40N120AN	FGH40N120AN	TO−247	–	–	30

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector to Emitter Breakdown Voltage	BV_{CES}	V_{GE} = 0 V, I_C = 1 mA	1200	–	–	V
Temperature Coefficient of Breakdown Voltage	$\Delta BV_{CES}/\Delta T_J$	V_{GE} = 0 V, I_C = 1 mA	–	0.6	–	V/°C
Collector Cut−Off Current	I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0 V	–	–	1	mA
G−E Leakage Current	I_{GES}	V_{GE} = V_{GES}, V_{CE} = 0 V	–	–	±250	nA
ON CHARACTERISTICs						
G−E Threshold Voltage	$V_{GE(th)}$	I_C = 250 μA, V_{CE} = V_{GE}	3.5	5.5	7.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 40 A, V_{GE} = 15 V	–	2.6	3.2	V
		I_C = 40 A, V_{GE} = 15 V, T_C = 125°C	–	2.9	–	V
		I_C = 64 A, V_{GE} = 15 V	–	3.15	–	V

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ies}	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	–	3200	–	pF
Output Capacitance	C_{oes}		–	370	–	pF
Reverse Transfer Capacitance	C_{res}		–	125	–	pF
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 600 V, I_C = 40 A, R_G = 5 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	–	15	–	ns
Rise Time	t_r		–	20	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	110	–	ns
Fall Time	t_f		–	40	80	ns
Turn−On Switching Loss	E_{on}		–	2.3	3.45	mJ
Turn−Off Switching Loss	E_{off}		–	1.1	1.65	mJ
Total Switching Loss	E_{ts}			3.4	5.1	mJ
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 600 V, I_C = 40 A, R_G = 5 Ω, V_{GE} = 15 V, Inductive Load, T_C = 125°C	–	20	–	ns
Rise Time	t_r		–	25	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	120	–	ns
Fall Time	t_f		–	45	–	ns
Turn−On Switching Loss	E_{on}		–	2.5	–	mJ
Turn−Off Switching Loss	E_{off}		–	1.8	–	mJ
Total Switching Loss	E_{ts}		–	4.3	–	mJ
Total Gate Charge	Q_g	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V	–	220	–	nC
Gate to Emitter Charge	Q_{ge}		–	25	–	nC
Gate to Collector Charge	Q_{gc}		–	130	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

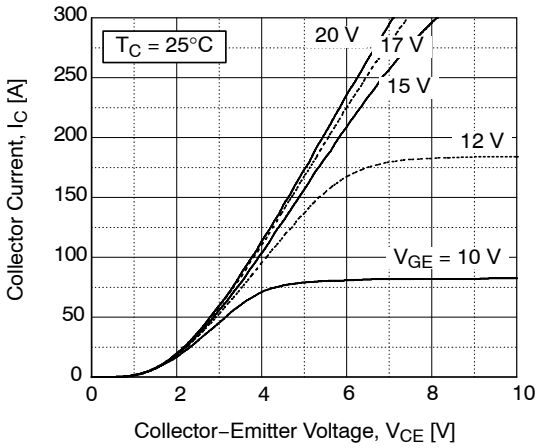


Figure 1. Typical Output Characteristics

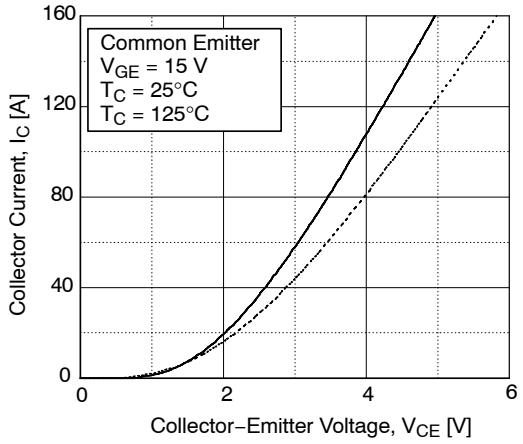


Figure 2. Typical Saturation Voltage Characteristics

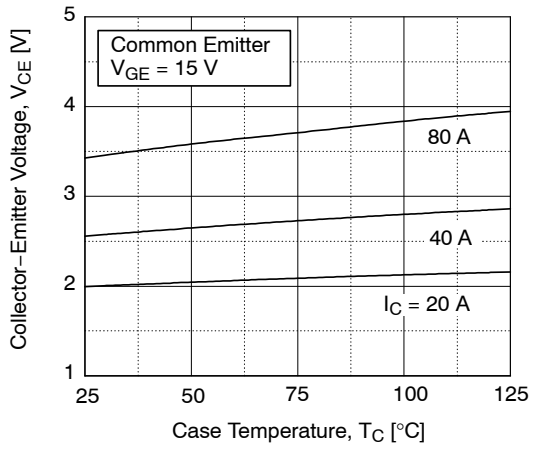


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

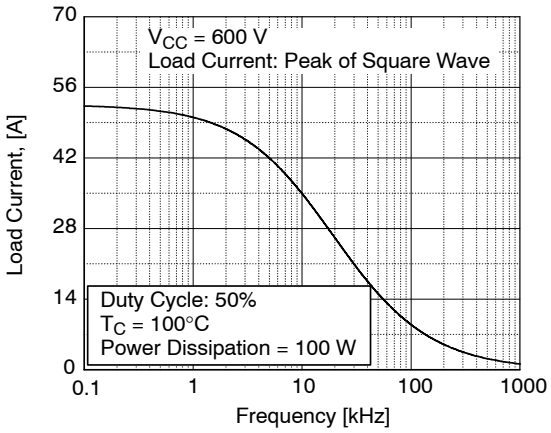


Figure 4. Load Current vs. Frequency

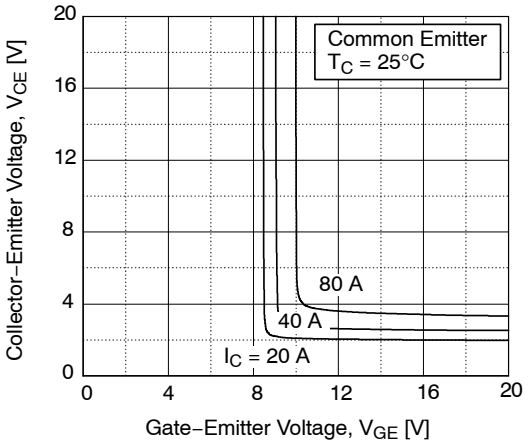


Figure 5. Saturation Voltage vs. V_{GE}

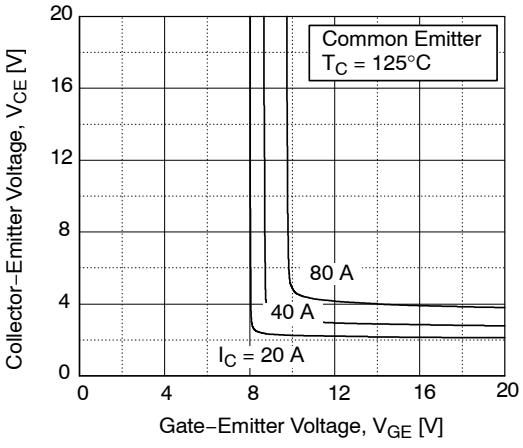


Figure 6. Saturation Voltage vs V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

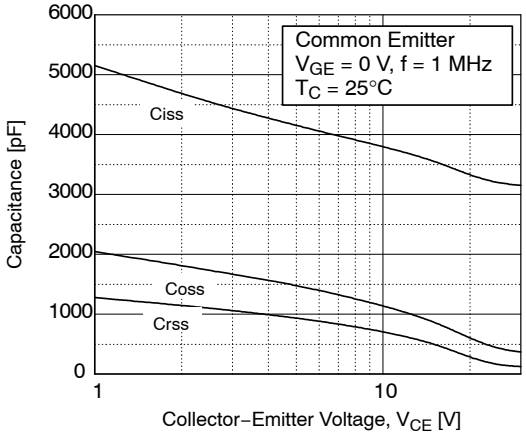


Figure 7. Capacitance Characteristics

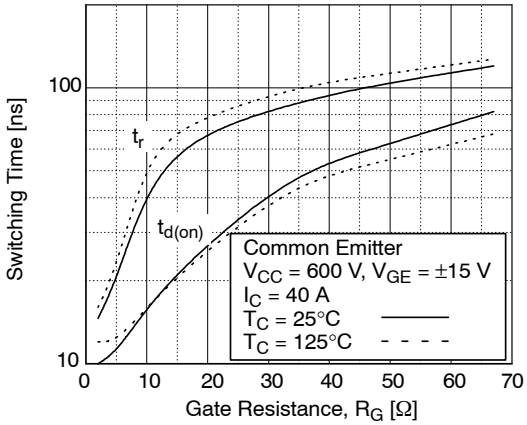


Figure 8. Turn−On Characteristic vs. Gate Resistance

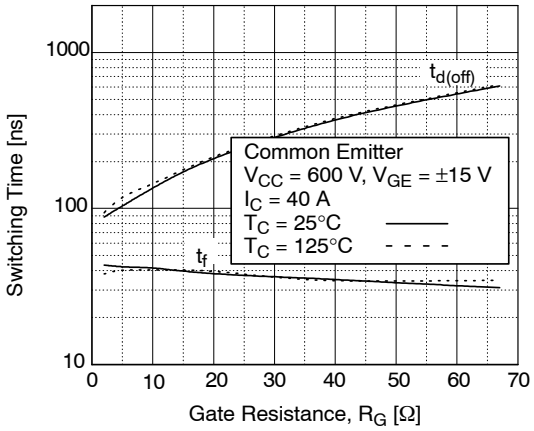


Figure 9. Turn−Off Characteristics vs. Gate Resistance

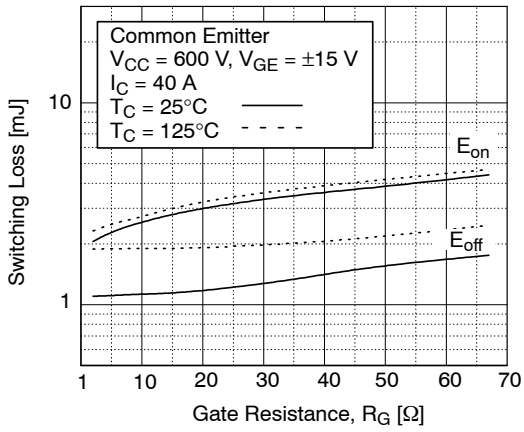


Figure 10. Switching Loss vs. Gate Resistance

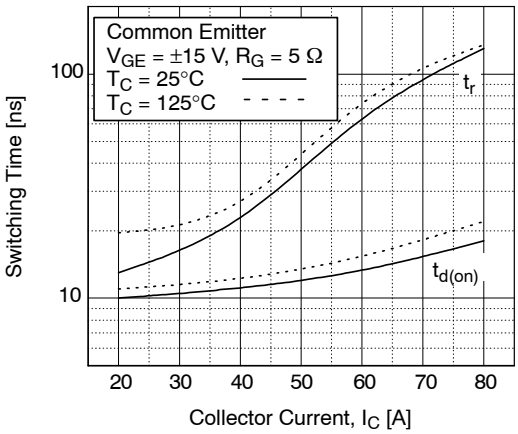


Figure 11. Turn−On Characteristics vs. Collector Current

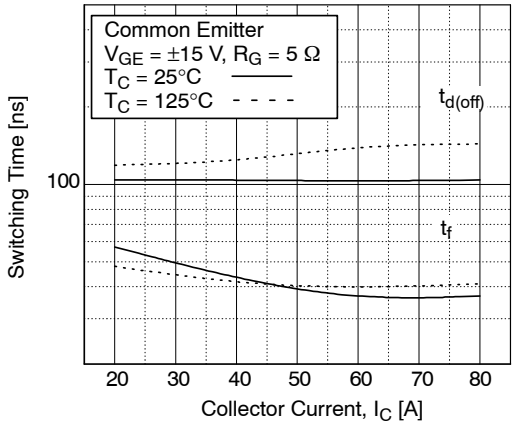


Figure 12. Turn−Off Characteristics vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

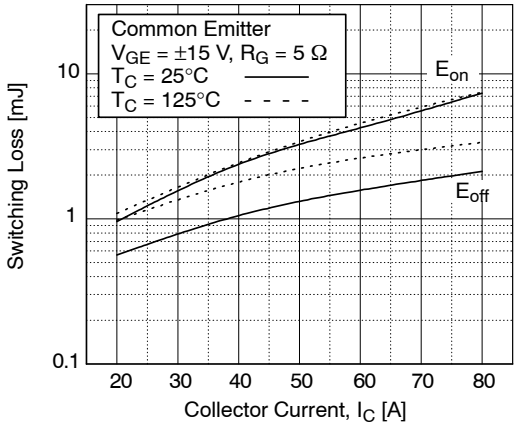


Figure 13. Switching Loss vs. Collector Current

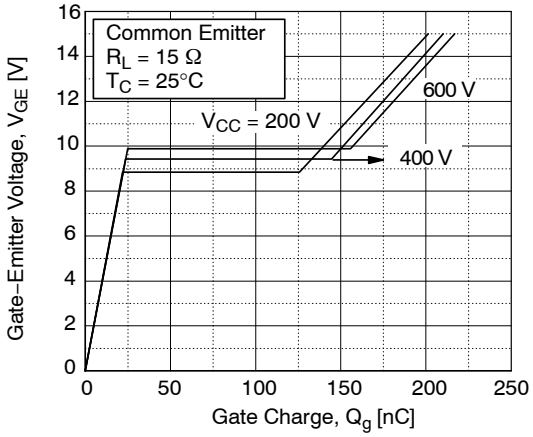


Figure 14. Gate Charge Characteristics

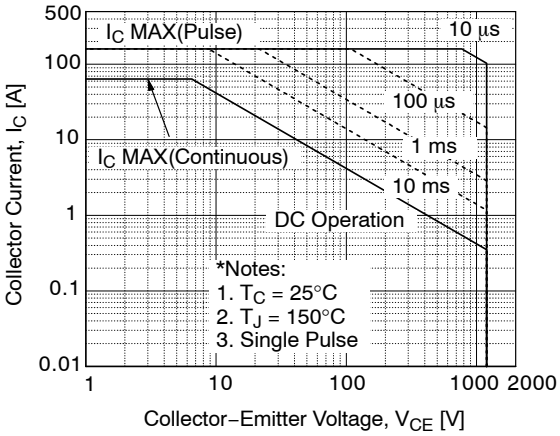


Figure 15. SOA Characteristics

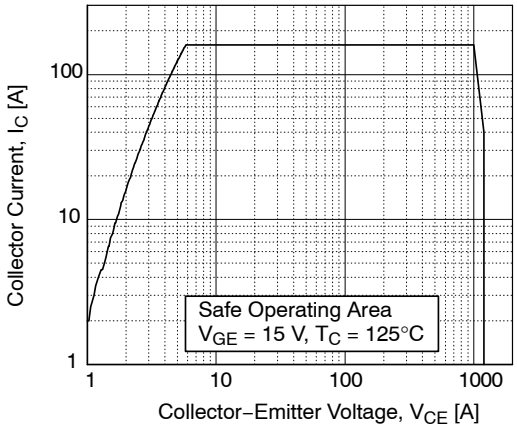


Figure 16. Turn−Off SOA

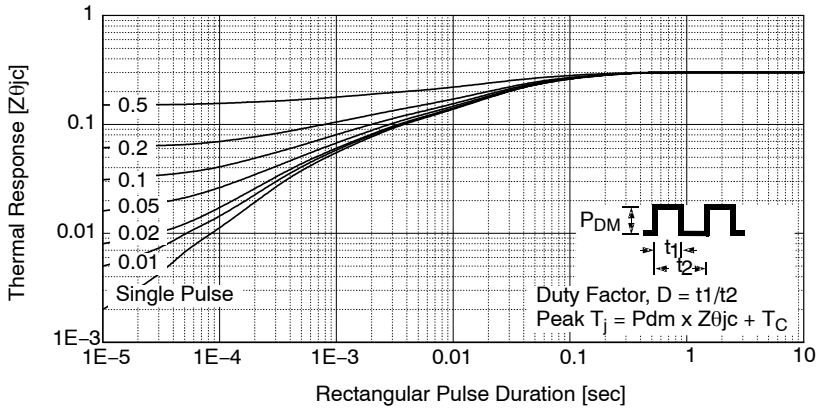
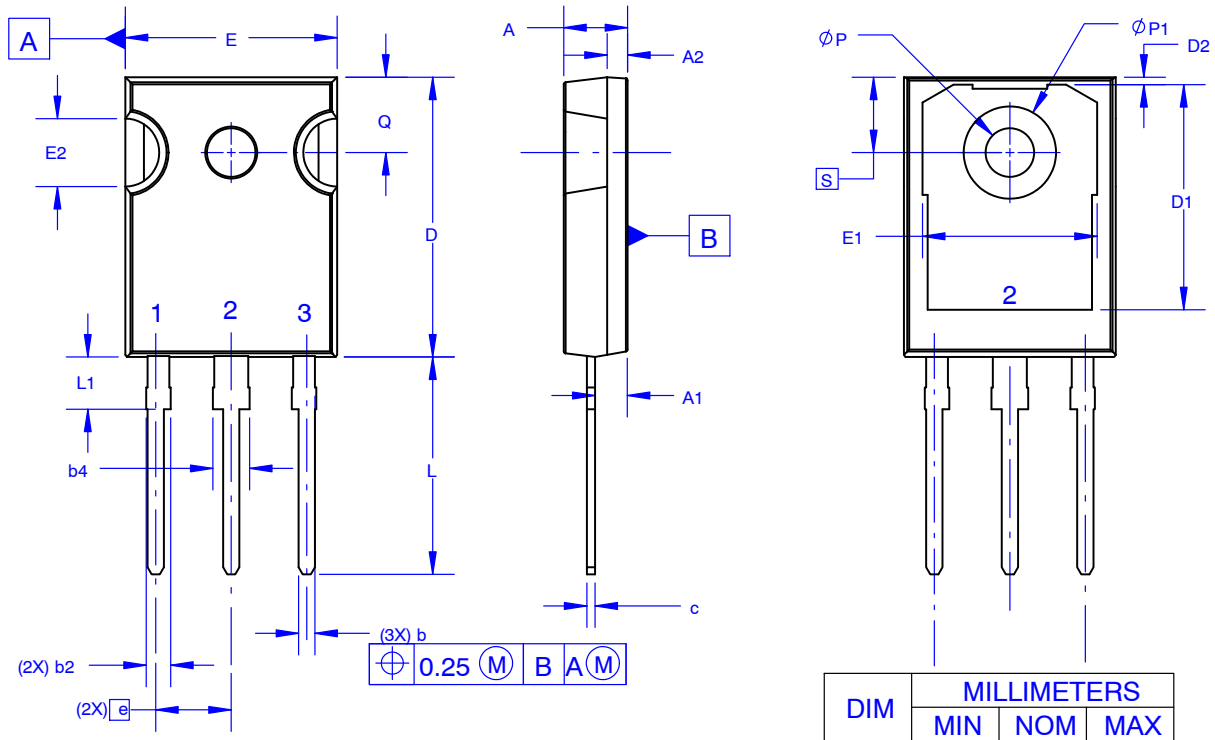


Figure 17. Transient Thermal Impedance of IGBT

TO−247−3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019

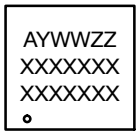


DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON13851G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**TO−247−3LD SHORT LEAD**	**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2016

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.